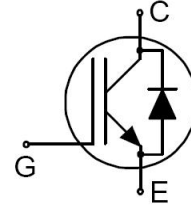


600V , 6A , Trench-FS IGBT

Features

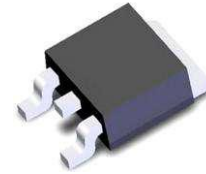
- ◆ Advanced Trench+FS (Field Stop) IGBT technology
- ◆ Low Collector-Emitter Saturation voltage, typical data is 2.1V @ 6A.
- ◆ Easy parallel switching capability due to positive Temperature coefficient in V_{ce} .
- ◆ 10uS Short-Circuit
- ◆ Fast switching
- ◆ High input impedance
- ◆ Pb- Free product



Schematic Diagram

Applications

- ◆ Home applications
- ◆ Intelligent power module.



TO-252

Electrical characteristics(T _J = 25°C unless otherwise noted)						
Symbol	Parameter	Test conditions	Units	Min.	Typ.	Max.
V _{(BR)CES}	Collector - Emitter breakdown voltage	V _{GE} = 0V, I _D =250uA	V	600	—	—
V _{CE(sat)}	Collector-Emitter Saturation voltage	V _{GE} =15V, I _C =6A,T _C =25°C	V	—	2.1	2.4
		V _{GE} =15V, I _C =6A,T _C =150°C	V	—	2.3	—
V _{GE(th)}	Gate threshold voltage	V _{GE} = V _{CE} , I _c = 0.25mA	V	4.0	5.4	6.5
V _F	Diode forward voltage	I _F =6A,T _C =25°C	V	—	1.7	2.1
		I _F =6A,T _C =150°C	V	—	1.3	—
I _{GES}	Gate to Emitter Forward Leakage	V _{ge} =+30V	nA	—	—	200
I _{GESR}	Gate to Emitter reverse Leakage	V _{ge} =-30V		-200	—	—
I _{CES}	Zero gate voltage collector current	V _{CE} =600V	uA	—	—	25